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Substitute for form 1449A/PTO
INFORMATION DISCLOSURE STATEMENT BY APPLICANT
(Use as many sheets as necessary)

Complete if Known

Application Number	10/623794
Filing Date	July 21, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2811 2823
Examiner Name	Unknown Michelle Estrada

Sheet 1 of 11

Attorney Docket No: 1303.108US1

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Michelle Estrada

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Substitute Disclosure Statement Form (PTO-1449)

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Examiner Name	Unknown M: Estrada

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Michele Estrada

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Sheet 3 of 11		Attorney Docket No: 1303.108US1				

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EXAMINER: *Michelle Estrada* **DATE CONSIDERED:** *1/4/05*

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		Group Art Unit	2811 2823
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EXAMINER *Michelle Estrada* DATE CONSIDERED *1/6/05*

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Sheet 5 of 11		Attorney Docket No: 1303.108US1	

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		First Named Inventor	Forbes, Leonard
		Group Art Unit	2811 2823
		Examiner Name	Unknown M. Estrada
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